**Product data sheet** 

## 1. General description

NPN low  $V_{CEsat}$  transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS4021PZ

### 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- · High collector current gain (hFE) at high IC
- · High energy efficiency due to less heat generation
- · Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

## 3. Applications

- Loadswitch
- · Battery-driven devices
- Power management
- · Charging circuits
- Power switches (e.g. motors, fans)

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	20	V
I <sub>C</sub>	collector current		-	-	8	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	20	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 6 A; $I_B$ = 600 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	14	20	mΩ



20 V, 8 A NPN low VCEsat transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	С
2	С	collector		
3	E	emitter		B — (
4	С	collector	1 2 3	Ė
			SC-73 (SOT223)	sym123

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
PBSS4021NZ		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	<u>SOT223</u>

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBSS4021NZ	PB4021
	NZ

20 V, 8 A NPN low VCEsat transistor

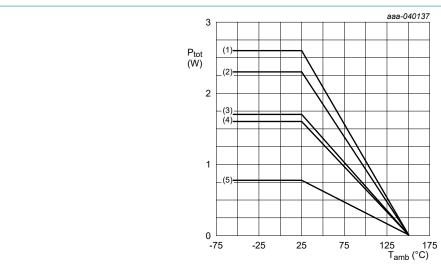
## 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	20	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	20	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
I <sub>C</sub>	collector current			-	8	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	20	Α
I <sub>B</sub>	base current			-	1	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.77	W
			[2]	-	1.7	W
			[3]	-	1.6	W
			[4]	-	2.3	W
			[5]	-	2.6	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- $[5] \quad \text{Device mounted on a ceramic PCB, Al}_2\text{O}_3, \text{ single-sided, 35} \ \mu\text{m copper, tin-plated and standard footprint.}$



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, single-sided, 35 µm copper, standard footprint
- (2) FR4 PCB, 4-layer copper, 1 cm<sup>2</sup>
- (3) FR4 PCB, single-sided, 35 µm copper, 6 cm<sup>2</sup>
- (4) FR4 PCB, 4-layer copper, standard footprint
- (5) FR4 PCB, single-sided, 35 µm copper, standard footprint

Fig. 1. Power derating curves

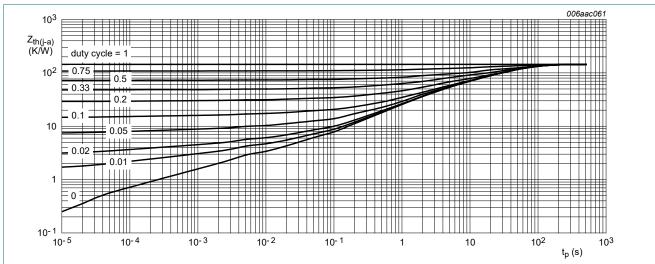
20 V, 8 A NPN low VCEsat transistor

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uiu-a)	thermal resistance from		[1]	-	-	160	K/W
	junction to ambient		[2]	-	-	75	K/W
			[3]	-	-	80	K/W
			[4]	-	-	55	K/W
			[5]	-	-	50	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	11	K/W

- [1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [5] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, single-sided, 35 μm copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

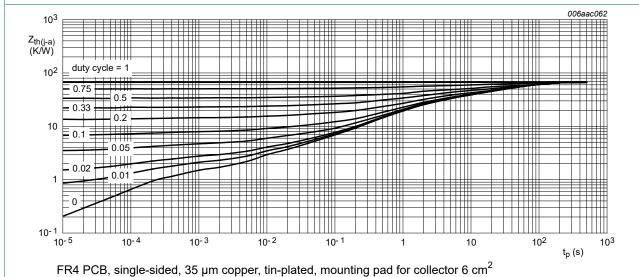
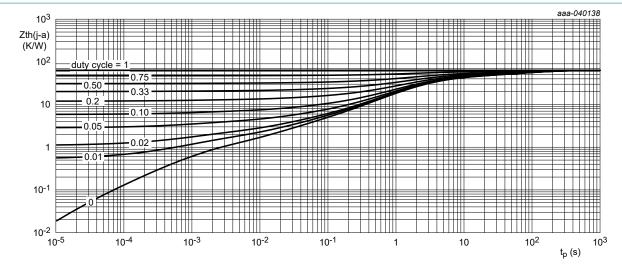


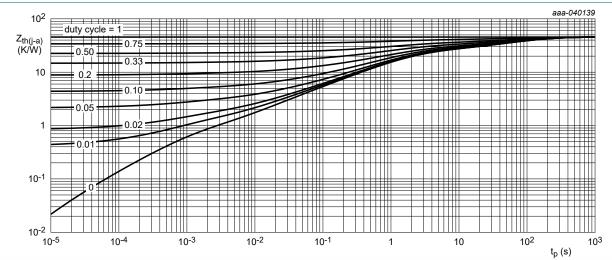
Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 20 V, 8 A NPN low VCEsat transistor



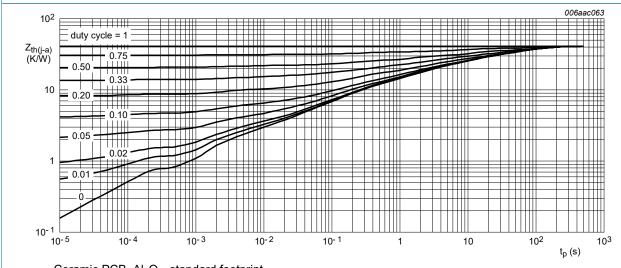
FR4 PCB, 4-layer, tin-plated and standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 20 V, 8 A NPN low VCEsat transistor

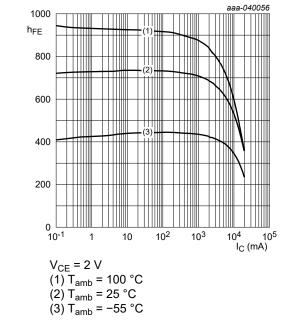
## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	20	-	-	V
/ <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = 10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	20	-	-	V
/ <sub>(BR)EBO</sub>	emitter-base breakdown voltage	$I_E = 100 \mu A; I_C = 0 A; T_{amb} = 25 °C$	5	-	-	V
СВО	collector-base cut-off	V <sub>CB</sub> = 20 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	50	μΑ
CES	collector-emitter cut-off current	V <sub>CE</sub> = 16 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
EBO	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
J <sup>EE</sup>	DC current gain	$V_{CE}$ = 2 V; $I_{C}$ = 500 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	300	620	-	V V V O NA
		$V_{CE}$ = 2 V; $I_{C}$ = 1 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	300	605	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 2 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	300	590	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 4 A; pulsed; $t_{p} \le 300 \ \mu s$ ; δ ≤ 0.02; $T_{amb}$ = 25 °C	250	550	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 8 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	250	480	-	
/ <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = 1 A; $I_B$ = 10 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	30	40	mV
		$I_C$ = 1 A; $I_B$ = 50 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	20	30	mV
		$I_C$ = 2 A; $I_B$ = 40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	40	55	mV
		$I_C$ = 4 A; $I_B$ = 40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	75	105	mV
		$I_C$ = 4 A; $I_B$ = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	60	85	mV
		$I_C$ = 8 A; $I_B$ = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	120	170	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 6 A; $I_B$ = 600 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	14	20	mΩ
/ <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = 1 A; $I_B$ = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	0.83	0.9	V
		$I_C$ = 4 A; $I_B$ = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	0.97	1.05	V
/ <sub>BE</sub>	base-emitter voltage	$V_{CE}$ = 2 V; $I_{C}$ = 2 A; pulsed; $t_{p} \le 300 \mu s$ ; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	0.73	0.85	V

### 20 V, 8 A NPN low VCEsat transistor

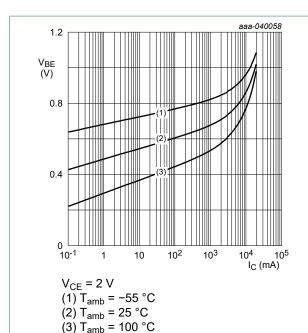
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>d</sub>	delay time	V <sub>CC</sub> = 12.5 V; I <sub>C</sub> = 1 A; I <sub>Bon</sub> = 0.05 A;	-	70	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -0.05 A; T <sub>amb</sub> = 25 °C	-	40	-	ns
t <sub>on</sub>	turn-on time		-	110	-	ns
t <sub>s</sub>	storage time		-	545	-	ns
t <sub>f</sub>	fall time		-	60	-	ns
t <sub>off</sub>	turn-off time		-	605	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	90	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C	-	116	-	pF



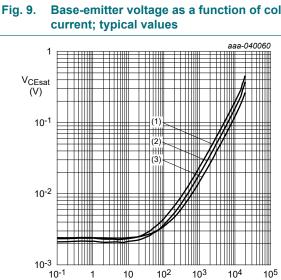
aaa-040057 20 I<sub>C</sub> (A)  $I_{B}$  (mA) = 42 37.8 16 33.6 29.4 25.2 12 21 16.8 8 12.6 8.4 4 4.2 4 V<sub>CE</sub> (V) 1 2 3  $T_{amb}$  = 25 °C

Fig. 8. Collector current as a function of collectoremitter voltage; typical values

#### 20 V, 8 A NPN low VCEsat transistor



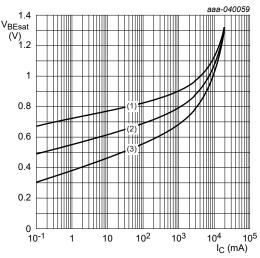
Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ (1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -55 °C

Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values



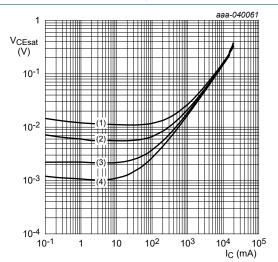
 $I_C/I_B = 20$ 

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb}$  = 25 °C

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

(1)  $I_C/I_B = 100$ 

(2)  $I_C/I_B = 50$ 

(3)  $I_C/I_B = 20$ 

(4)  $I_C/I_B = 10$ 

Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values

#### 20 V, 8 A NPN low VCEsat transistor

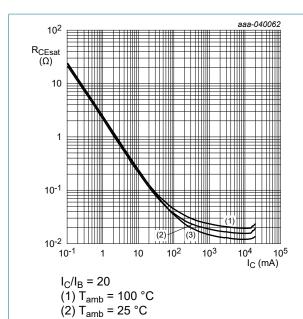
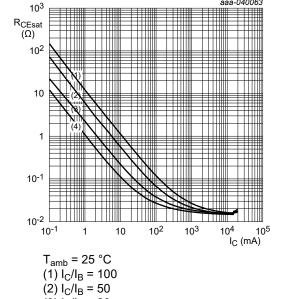


Fig. 13. Collector-emitter saturation resistance as a function of collector current; typical values

(3)  $T_{amb} = -55 \, ^{\circ}C$ 



(2)  $I_C/I_B = 50$ (3)  $I_C/I_B = 20$  $(4) I_{\rm C}/I_{\rm B} = 10$ 

Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values

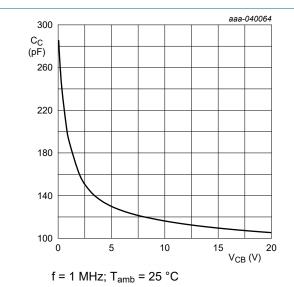
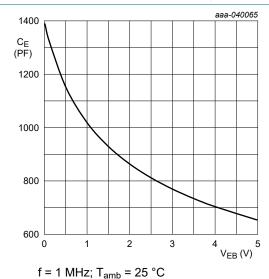


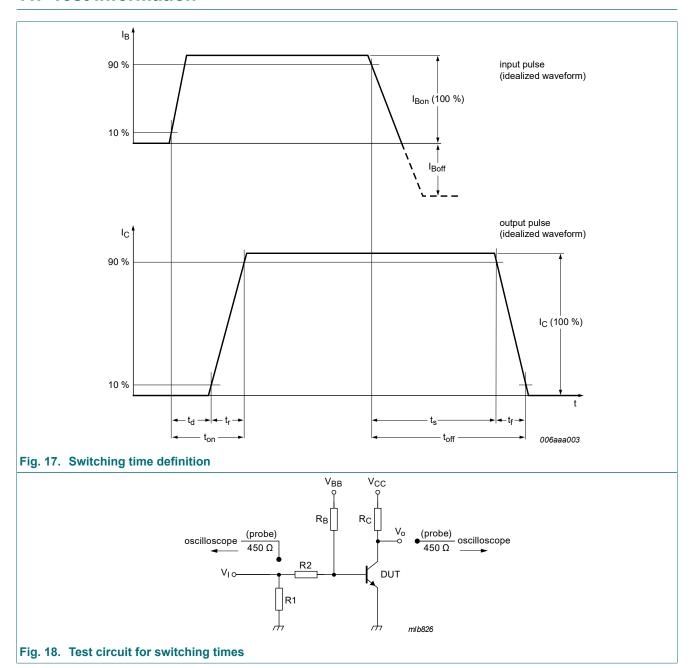
Fig. 15. Collector capacitance as a function of collector- Fig. 16. Emitter capacitance as a function of emitterbase voltage; typical values



base voltage; typical values

20 V, 8 A NPN low VCEsat transistor

## 11. Test information

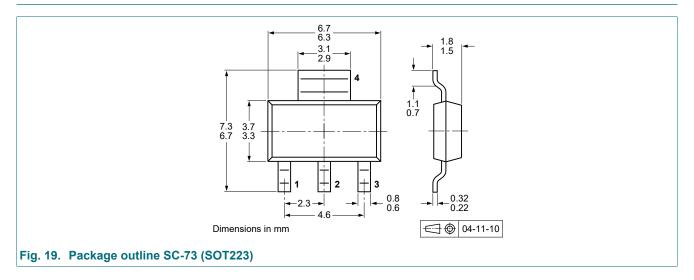


### **Quality information**

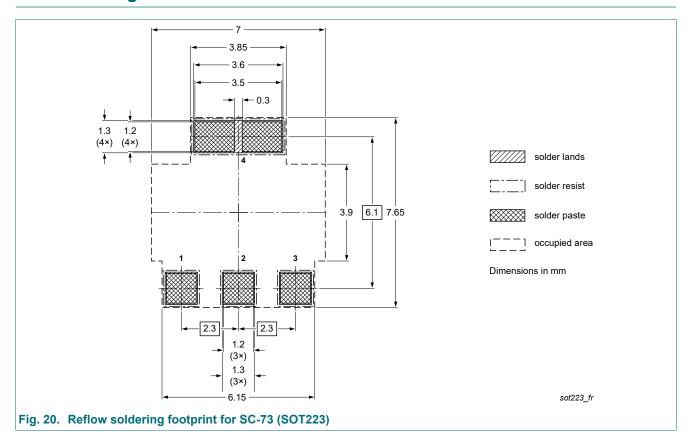
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

20 V, 8 A NPN low VCEsat transistor

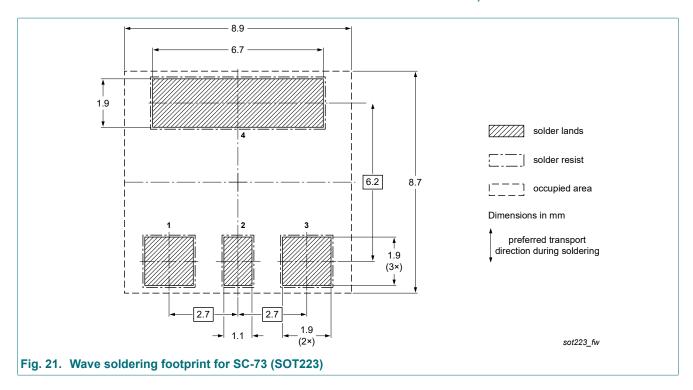
# 12. Package outline



## 13. Soldering



### 20 V, 8 A NPN low VCEsat transistor



## 20 V, 8 A NPN low VCEsat transistor

# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS4021NZ v.2	20240920	Product data sheet	-	PBSS4021NZ v.1	
Modifications:	<ul><li>New graphs added, graphs updated and values changed.</li><li>Section "Packing information" removed.</li></ul>				
PBSS4021NZ v.1	20100331	Product data sheet	-	-	

#### 20 V, 8 A NPN low VCEsat transistor

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PBSS4021N2

## 20 V, 8 A NPN low VCEsat transistor

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	Features and benefits

For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 20 September 2024

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